

QRD4518001

Dual Diode Isolated Module 180 Amperes/4500 Volts



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters		
А	5.51	140.0		
В	2.87	73.0		
С	1.89	48.0		
D	4.88±0.01	124.0±0.25		
E	2.24±0.01	57.0±0.25		
F	1.18	30.0		
G	0.43	11.0		

Dimensions	Inches	Millimeters		
М	0.38	9.75		
Ν	0.20	5.0		
Q	1.44	36.5		
R	0.16	4.0		
S	M6 Metric	M6		
Т	0.63 Min.	16.0 Min.		
V	0.28 Dia.	7.0 Dia.		



Description:

High voltage diodes feature highly insulating housings that offer enhanced protection by means of greater creepage and strike clearance distance for many demanding applications like medium voltage drives and auxiliary traction applications.

Features:

- Aluminum Nitride (AIN) Ceramic Substrate for Low Thermal Impedance
- Copper Baseplate
- Industry Standard Packages Allow Common Bus Work to Complementary High Isolation Diodes
- No Additional Insulation Components Required

Applications:

- Diodes for 18-24 Pulse Front End Rectifiers in 10.2 KV Isolation
- □ High Voltage Power Supplies
- □ Medium Voltage Drives
- □ Motor Drives
- □ Traction



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Absolute Maximum Ratings, T_{j} = 25 °C unless otherwise specified

Ratings		Symbol	QRD4518001	Units
Repetitive Peak Reverse Blocking Voltage	V _{RRM}	4500	Volts	
Non-Repetitive Peak Reverse Blocking Voltage (t <	Ion-Repetitive Peak Reverse Blocking Voltage (t < 5 msec)			Volts
RMS Forward Current		I _{F(RMS)}	282	Amperes
Average Forward Current (180° Conduction, $T_C =$	95°C)	I _{F(AV)}	180	Amperes
Peak One Cycle Surge Current, Non-Repetitive	60 Hz, 100% V _{RRM} Reapplied	I _{FSM}	3860	Amperes
	50 Hz, 100% V _{RRM} Reapplied	I _{FSM}	3475	Amperes
	60 Hz, No V _{RRM} Reapplied	IFSM	5800	Amperes
	50 Hz, No V _{RRM} Reapplied	IFSM	5215	Amperes
I ² t for Fusing for One Cycle	8.3 Milliseconds	l ² t	140,000	A ² sec
	10 Milliseconds	l ² t	151,000	A ² sec
Operating Temperature		Тj	-40 to 150	°C
Storage Temperature		T _{stg}	-40 to 150	°C
Maximum Mounting Torque, M6 Mounting Screws		_	44	in-lb
			5.0	Nm
Maximum Mounting Torque, M6 Terminal Screws		_	— 44	
			5.0	Nm
Module Weight (Typical)		_	750	Grams
			1.65	Pounds
Isolation Voltage (@ 25°C, 60Hz, 1 min.)		V _{rms}	10.2	kV



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Electrical Characteristics, $T_j = 25$ °C unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Тур.	Max.	Units
Repetitive Peak Reverse Leakage Current	I _{RRM}	V_{RRM} = 4500V, T_{j} = 150°C	_	—	30	mA
Peak On-State Voltage	VFM	$T_j = 150^{\circ}C, I_{FM} = 180A$	_	_	1.35	Volts
Threshold Voltage (Low-Level)	V _{(TO)1}	$T_j = 150^{\circ}C$, I = 15% I _{F(AV)} to \prod I _{F(AV})	_	—	0.27	Volts
Slope Resistance (Low-Level)	r _{T1}		_	_	5.216	mΩ
Threshold Voltage (High-Level)	V _{(TO)2}	$T_j = 150^{\circ}C$, $I = \prod I_{F(AV)}$ to I_{FSM}				Volts
Slope Resistance (High-Level)	r _{T2}					mΩ
V _{TM} Coefficients (Full Range)		$T_j = 150^{\circ}C$, I = 15% I _{F(AV)} to I _{FSM}	A = 0.726			
			B = -577E-07			
		V _{TM} = A + B Ln I + CI + D Sqrt I		C = 5.22E	-03	
				D = -3.08	E-07	

Thermal and Mechanical Characteristics, $T_j = 25$ °C unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	R _{th(j-c)}	Per Diode	—	—	0.099	°C/W
Thermal Impedance Coefficients	Z _{th(j-c)}	$Z_{th(j-c)} = K_1 (1-exp(-t/\tau_1))$	K ₁ = 1.34	1E-04	τ ₁ = 1.95E-0	03
		+ $K_2 (1-exp(-t/\tau_2))$	K ₂ = 8.29	9E-03	$\tau_2 = 4.90 \text{E-}0$	03
		+ $K_3 (1-exp(-t/\tau_3))$	K ₃ = 1.36	6E-02	$\tau_3 = 5.18E-0$	02
		+ K ₄ (1-exp(-t/τ ₄))	K ₄ = 7.89	9E-02	$\tau_4 = 0.221$	
Thermal Resistance,	R _{th(c-s)}	Thermal Grease Applied	_	_	0.018	°C/W
Case to Sink Lubricated		$\lambda_{grease} = 1 \text{ W/mK}$				



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